

#### **Description**

The TN2106K uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.

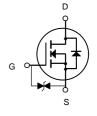


#### **General Features**

 $V_{DS} = 60V I_{D} = 0.3A$ 

 $R_{DS(ON)} < 2\Omega$  @  $V_{GS}=10V$ 

ESD Rating: HBM≥2000V



N-Channel MOSFET

#### **Application**

Battery protection

Load switch

Uninterruptible power supply

#### **Package Marking and Ordering Information**

| Product ID | Pack   | Brand      | Qty(PCS) |
|------------|--------|------------|----------|
| TN2106K    | SOT-23 | HXY MOSFET | 3000     |

#### Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

| Symbol                           | Parameter  |                      | Limit      | Unit         |
|----------------------------------|--|----------------------|------------|--------------|
| V <sub>DS</sub>                  | Drain-Source Voltage                             |                      | 60         | ٧            |
| V <sub>G</sub> S                 | Gate-Source Voltage                              |                      | ±20        | V            |
|                                  |  | T <sub>A</sub> =25℃  | 0.3        |              |
| l <sub>D</sub>                   | Continuous Drain Current (T <sub>J</sub> =150°C) | T <sub>A</sub> =100℃ | 0.19       | Α            |
| <b>I</b> DM                      | Drain Current-Pulsed (Note 1)                    |                      | 0.8        | Α            |
| P <sub>D</sub>                   | Maximum Power Dissipation                        |                      | 0.35       | W            |
| T <sub>J</sub> ,T <sub>STG</sub> | Operating Junction and Storage Temperature Range |                      | -55 To 150 | $^{\circ}$ C |
| Reja                             | Thermal Resistance,Junction-to-Ambient (Note 2)  |                      | 350        | °C/W         |



# Electrical Characteristics (T<sub>A</sub>=25℃unless otherwise noted)

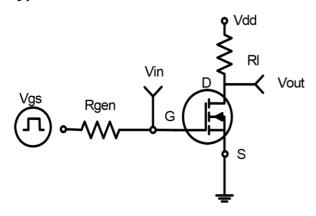
| Parameter Parameter              | Symbol              | Condition                                  | Min | Тур  | Max  | Unit |
|----------------------------------|---------------------|--|-----|------|------|------|
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250µA  | 60  | 68   | -    | V    |
| Zero Gate Voltage Drain Current  | IDSS                | V <sub>DS</sub> =60V,V <sub>GS</sub> =0V   | -   | -    | 1    | μΑ   |
| Gate-Body Leakage Current        | Igss                | V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V  | -   | ±100 | ±500 | nA   |
|                                  |                     | V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V  | -   | ±4   | ±10  | uA   |
| Gate Threshold Voltage           | V <sub>GS(th)</sub> | $V_{DS}=V_{GS}$ , $I_{D}=250\mu A$         | 0.7 | 1.2  | 1.9  | V    |
|                                  |                     | V <sub>GS</sub> =5V, I <sub>D</sub> =0.1A  | -   | 1.3  | 3    | Ω    |
| Drain-Source On-State Resistance | Rds(on)             | V <sub>GS</sub> =10V, I <sub>D</sub> =0.1A | -   | 1    | 2    | Ω    |
| Forward Transconductance         | <b>g</b> FS         | V <sub>DS</sub> =10V,I <sub>D</sub> =0.2A  | 0.1 | -    | -    | S    |
| Input Capacitance                | C <sub>lss</sub>    |  | -   | 21   | 50   | PF   |
| Output Capacitance               | Coss                | $V_{DS}$ =25V, $V_{GS}$ =0V,<br>F=1.0MHz   | -   | 11   | 25   | PF   |
| Reverse Transfer Capacitance     | C <sub>rss</sub>    | 1 – 1.0WII 12                              | -   | 4.2  | 5    | PF   |
| Turn-on Delay Time               | td(on)              |  | -   | 10   | -    | nS   |
| Turn-on Rise Time                | t <sub>r</sub>      | V <sub>DD</sub> =30V,I <sub>D</sub> =0.2A  | -   | 50   | -    | nS   |
| Turn-Off Delay Time              | td(off)             | $V_{GS}=10V,R_{GEN}=10\Omega$              | -   | 17   | -    | nS   |
| Turn-Off Fall Time               | t <sub>f</sub>      |  | -   | 10   | -    | nS   |
|                                  |                     | $V_{DS}$ =10 $V$ , $I_{D}$ =0.3 $A$ ,      |     |      |      |      |
| Total Gate Charge                | $Q_g$               | V <sub>GS</sub> =4.5V                      | -   | 1.7  | 3    | nC   |
| Diode Forward Voltage (Note 3)   | Vsp                 | V <sub>GS</sub> =0V,I <sub>S</sub> =0.2A   | -   | -    | 1.2  | V    |
| Diode Forward Current (Note 2)   | Is                  |  | -   | -    | 0.3  | Α    |

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



### **Typical Electrical And Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

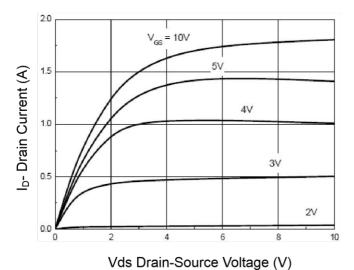


Figure 3 Output Characteristics

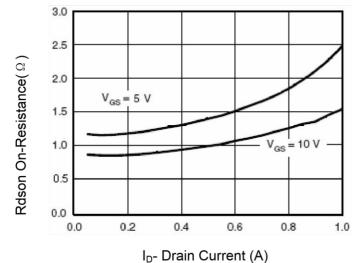


Figure 5 Drain-Source On-Resistance

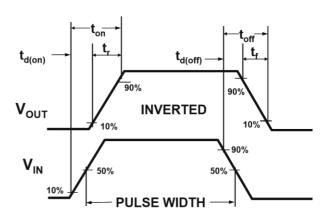


Figure 2:Switching Waveforms

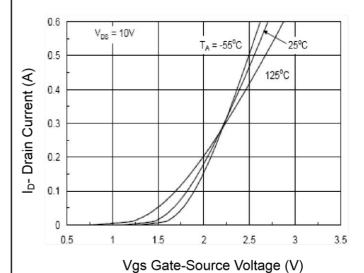
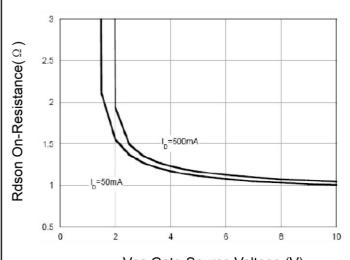
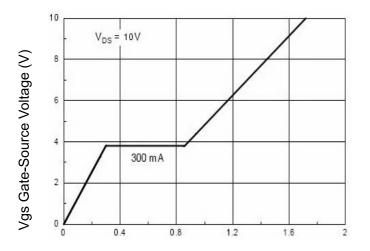


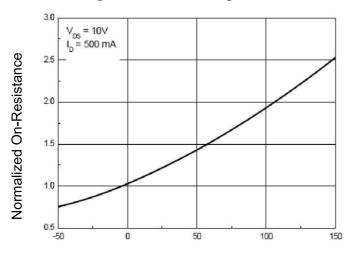
Figure 4 Transfer Characteristics



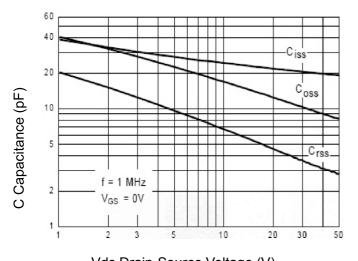
Vgs Gate-Source Voltage (V)
Figure 6 Rdson vs Vgs



Qg Gate Charge (nC) Figure 7 Gate Charge



 $T_J$ -Junction Temperature( ${}^{\circ}C$ )
Figure 9 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds

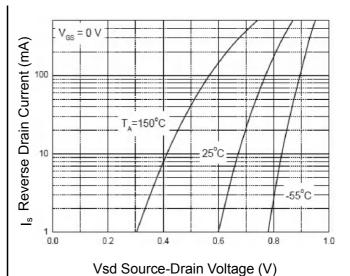
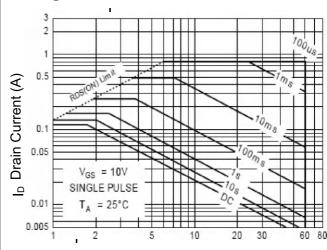
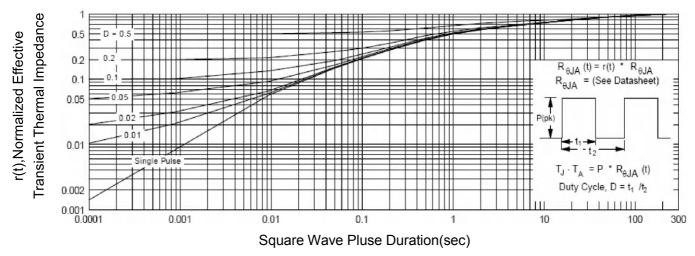


Figure 8 Source-DrainDiode Forward



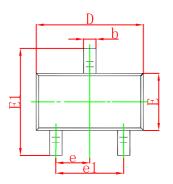
Vds Drain-Source Voltage (V)
Figure 10 Safe Operation Area

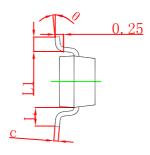


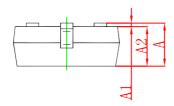
**Figure 12 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Outline Dimensions**

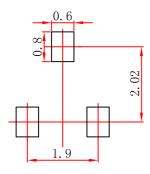






| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
|        | Min                       | Max   | Min                  | Max   |  |
| Α      | 0.900                     | 1.150 | 0.035                | 0.045 |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |  |
| A2     | 0.900                     | 1.050 | 0.035                | 0.041 |  |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |  |
| С      | 0.080                     | 0.150 | 0.003                | 0.006 |  |
| D      | 2.800                     | 3.000 | 0.110                | 0.118 |  |
| E      | 1.200                     | 1.400 | 0.047                | 0.055 |  |
| E1     | 2.250                     | 2.550 | 0.089                | 0.100 |  |
| е      | 0.950                     | TYP   | 0.037                | 7 TYP |  |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |  |
| L      | 0.550                     | REF   | 0.022 REF            |       |  |
| L1     | 0.300                     | 0.500 | 0.012                | 0.020 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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